General Description:

HMM140J65 the silicon N-channel Enhanced VDMOSFETS, is obtained by the advanced trench gate super junction technolog which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency. The package form is SOT-227B, which accords with the RoHS standard.

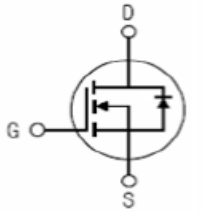
$V_{DSS}(T_J=150℃)$	700	V
$V_{DSS}(T_C=150℃)$	650	V
I_D	140	A
$P_D(T_C=25℃)$	1560	W
$R_{DS(ON)TYP}$	18	mΩ

SOT-227B

Features:

- Proprietary New Super-Junction Technology
- $R_{DS(ON).typ.}$=18mΩ
- Low Gate Charge Minimize Switching Loss
- 100% Single Pulse avalanche energy Test

Inner Equivalent Principium Chart



Applications:

- Adaptor
- Charger
- SMPS Standby Power
- Switching Voltage Regulators

Absolute (Tc= 25℃ unless otherwise specified):

Symbol	Parameter	Rating	Units
V_{DSS}	Drain-to-Source Voltage	650	V
I_D	Continuous Drain Current	140	A
I_{DM}	Pulsed Drain Current	560	A
	Pulsed Drain Current (Pulse Width Limited by T_{JM})	240	A
V_{GS}	Gate-to-Source Voltage	±30	V
E_{AS}	Single Pulse Avalanche Energy	2	J
P_D	Power Dissipation	1560	W
	Derating Factor above 25°C	12.48	W/℃
T_J, T_{stg}	Operating Junction and Storage Temperature Range	150, −55 to 150	℃
T_L	Maximum Temperature for Soldering	300	℃

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Electrical Characteristics (Tc=25℃ unless otherwise specified):

OFF Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	V_{GS}=0V,I_D=250μA	650	--	--	V
I_{DSS}	Drain to Source Leakage Current	V_{DS}=650V, V_{GS}=0V, T_a=25℃	--	--	10	μA
		V_{DS}=520V, V_{GS}=0V, T_a=125℃	--	--	1000	
$I_{GSS(F)}$	Gate to Source Forward Leakage	V_{GS}=+30V	--	--	300	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	V_{GS}=-30V	--	--	-300	nA

ON Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$R_{DS(ON)}$	Drain-to-Source On-Resistance	V_{GS}=10V,I_D=70A	--	18	25	mΩ
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	3.0	--	5.0	V
g_{fs}	Forward Transconductance	V_{DS}=10V, I_D=70A	--	60	--	S
Pulse width tp≤380μs,δ≤2%						

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
C_{iss}	Input Capacitance	V_{GS}= 0V V_{DS}=100V f=1.0MHz	--	16000	--	pF
C_{oss}	Output Capacitance		--	600	--	
C_{rss}	Reverse Transfer Capacitance		--	80	--	
Q_g	Total Gate Charge	I_D=50A,V_{DD}=520V V_{GS}=0 to 10V	--	320	--	nc
Q_{gs}	Gate to Source Charge		--	100	--	nc
Q_{gd}	Gate to Drain (“Miller”)Charge		--	130	--	nc

Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	V_{DD}=300V,I_D=50A, V_{GS}=10V R_g=25Ω	--	110	--	nS
tr	Rise Time		--	90	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	600	--	
t_f	Fall Time		--	105	--	

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
I_S	Continuous Source Current (Body Diode)		--	--	100	A
I_{SM}	Maximum Pulsed Current (Body Diode)		--	--	240	A
V_{SD}	Diode Forward Voltage	I_S=100A,V_{GS}=0V	--	--	1.5	V
t_{rr}	Reverse Recovery Time	V_R=480V, I_F=I_S, diF/dt=100A/us, V_{GS}=0V	--	150	--	ns
Q_{rr}	Reverse Recovery Charge		--	1.3	--	uC
Pulse width tp≤380μs,δ≤2%						

Symbol	Parameter	Max.	Units
$R_{\theta JC}$	Junction-to-Case	0.08	℃/W
$R_{\theta JA}$	Junction-to-Ambient	55	℃/W

TJ=+25℃ to +150℃

Pulse width≤380μs; duty cycle≤2%.